BYQ28X-200

Dual ultrafast rugged rectifier diode

Rev. 02 — 5 February 2009 Product data sheet

1. Product profile

1.1 General description

Dual ultrafast epitaxial rectifier diodes in a SOT186A (TO-220F) isolated plastic package.

1.2 Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state losses
- Soft recovery minimizes power-consuming oscillations

1.3 Applications

- Output rectifiers in high-frequency switched-mode power supplies

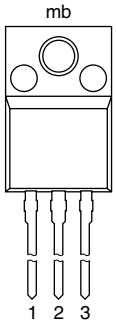
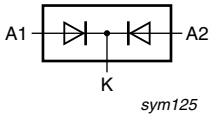
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	200	V
$I_{O(AV)}$	average output current	SQW; δ = 0.5; $T_h \leq 92$ °C; both diodes conducting; see Figure 1; see Figure 2	-	-	10	A
I_{FRM}	repetitive peak forward current	SQW; δ = 0.5; t_p = 25 µs; $T_h \leq 92$ °C; per diode	-	-	10	A
Dynamic characteristics						
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; ramp recovery; see Figure 5	-	15	25	ns
Static characteristics						
V_F	forward voltage	I_F = 5 A; T_j = 150 °C; see Figure 4	-	0.8	0.895	V
Electrostatic discharge						
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	-	-	8	kV

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode		
3	A2	anode 2		
mb	n.c.	mounting base; isolated		

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

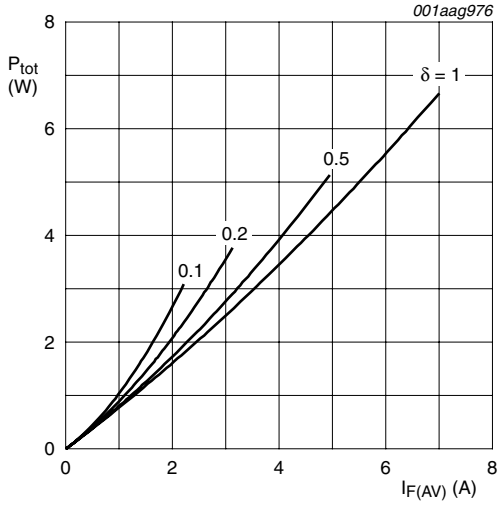
Type number	Package		
	Name	Description	Version
BYQ28X-200	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

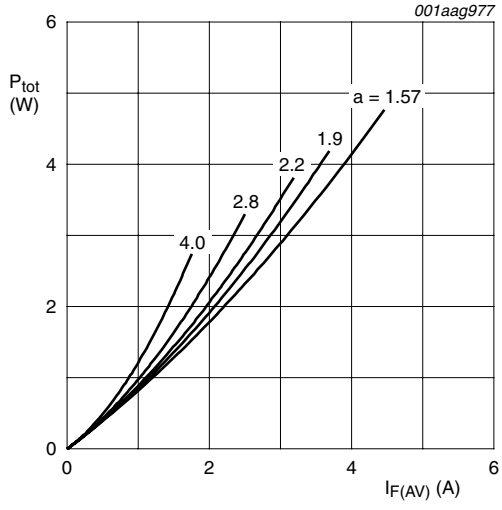
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_R	reverse voltage	DC	-	200	V
$I_{O(AV)}$	average output current	SQW; δ = 0.5; $T_h \leq 92$ ℃; both diodes conducting; see Figure 1; see Figure 2	-	10	A
I_{FRM}	repetitive peak forward current	SQW; δ = 0.5; t_p = 25 µs; $T_h \leq 92$ ℃; per diode	-	10	A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; SIN; $T_{j(init)}$ = 25 ℃; per diode	-	50	A
		t_p = 8.3 ms; SIN; $T_{j(init)}$ = 25 ℃; per diode	-	55	A
I_{RRM}	repetitive peak reverse current	t_p = 2 µs; δ = 0.001	-	0.2	A
I_{RSM}	non-repetitive peak reverse current	t_p = 100 µs	-	0.2	A
T_{stg}	storage temperature		-40	150	℃
T_j	junction temperature		-	150	℃
Electrostatic discharge					
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	-	8	kV



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	-	5.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	55	-	K/W

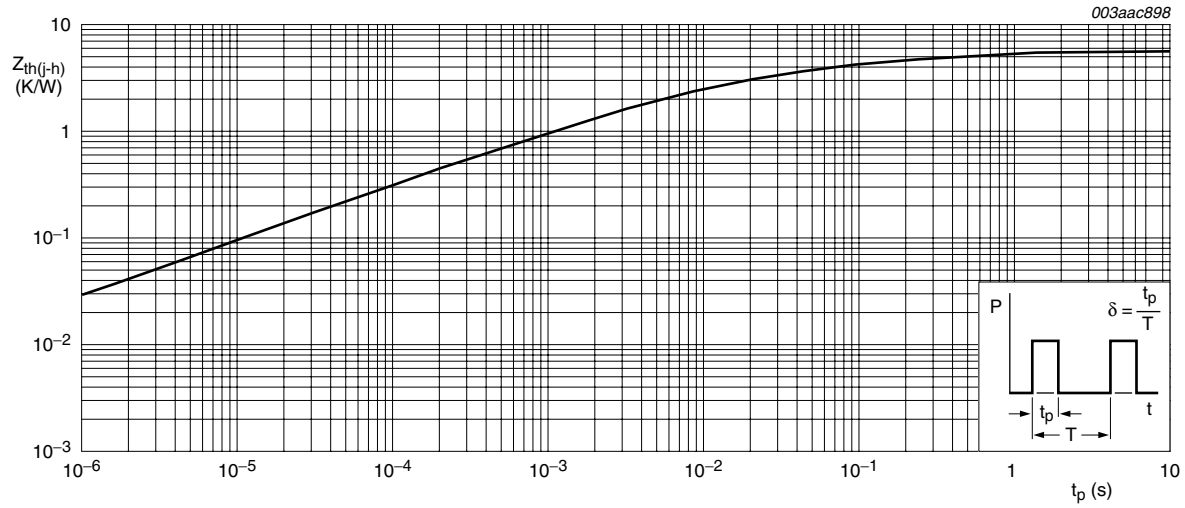


Fig 3. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

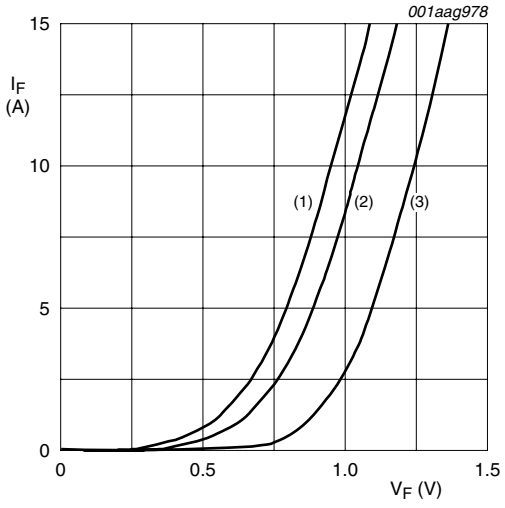
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	I_F = 10 A; T_j = 25 °C	-	1.1	1.25	V
		I_F = 5 A; T_j = 150 °C; see Figure 4	-	0.8	0.895	V
		I_F = 5 A; T_j = 25 °C	-	0.95	1.1	V
I_R	reverse current	V_R = 200 V; T_j = 25 °C	-	2	10	µA
		V_R = 200 V; T_j = 100 °C	-	0.1	0.2	mA
Dynamic characteristics						
Q_r	recovered charge	I_F = 2 A; V_R = 30 V; dI_F/dt = 20 A/µs; T_j = 25 °C	-	4	9	µC
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; ramp recovery; T_j = 25 °C; see Figure 5	-	15	25	ns
		I_F = 0.5 A; I_R = 1 A; step recovery; measured at I_R = 0.25 A; T_j = 25 °C; see Figure 6	-	-	20	ns
I_{RM}	peak reverse recovery current	I_F = 5 A; $V_R \geq$ 30 V; dI_F/dt = 50 A/µs; T_j = 25 °C; see Figure 5	-	0.5	0.7	A
V_{FRM}	peak forward recovery voltage	I_F = 1 A; dI_F/dt = 10 A/µs; T_j = 25 °C; see Figure 7	-	1	-	V



(1) $T_j = 150\ °C$; typical values
(2) $T_j = 150\ °C$; maximum values
(3) $T_j = 25\ °C$; maximum values

Fig 4. Forward current as a function of forward voltage

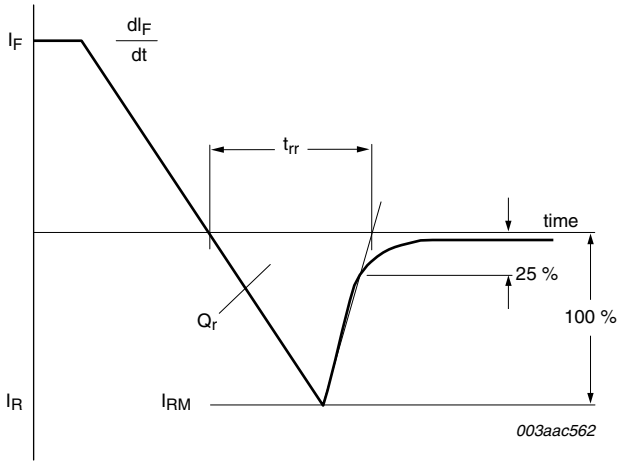


Fig 5. Reverse recovery definitions; ramp recovery

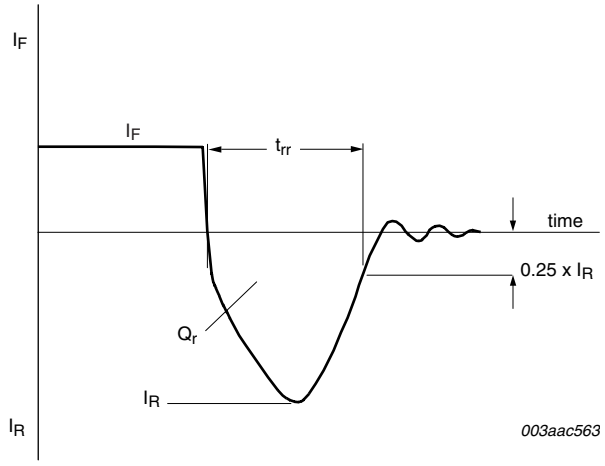


Fig 6. Reverse recovery definitions; step recovery

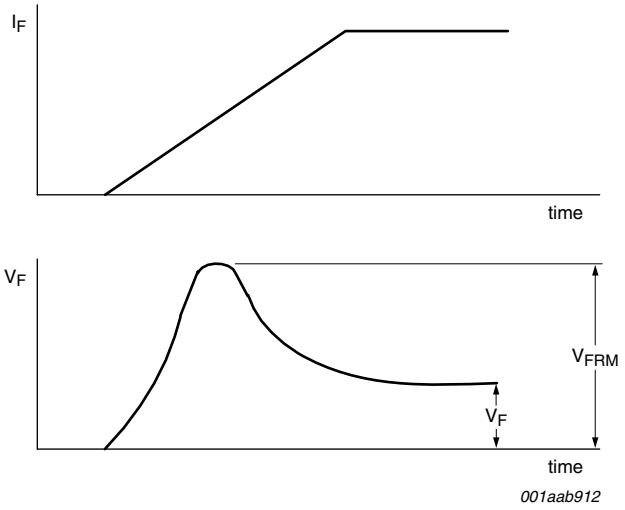
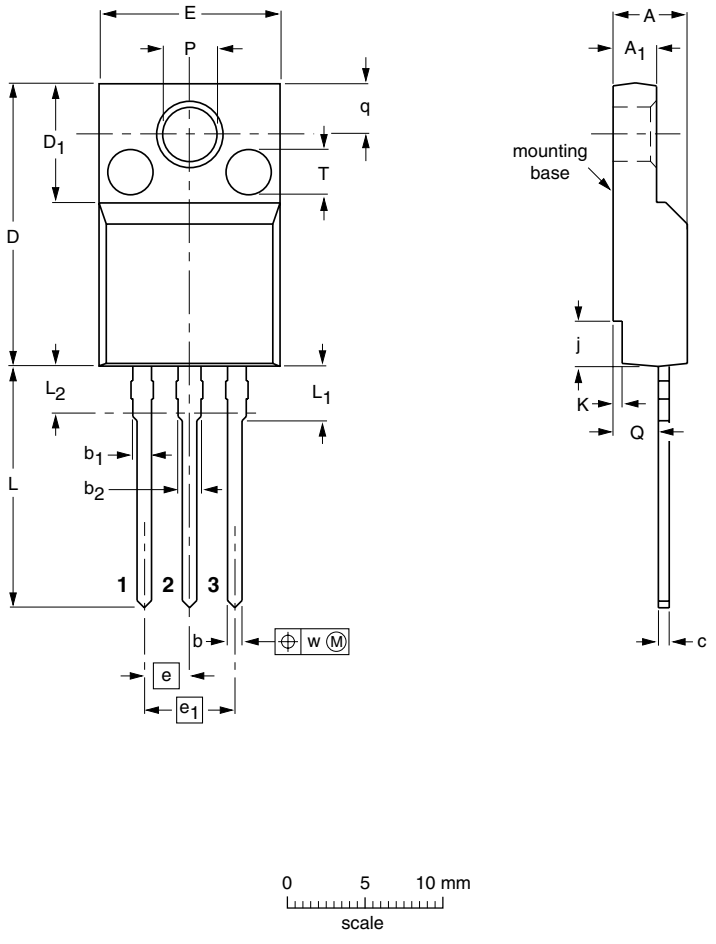


Fig 7. Forward recovery definitions

8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	b_2	c	D	D_1	E	e	e_1	j	K	L	L_1	L_2 (1) max.	P	Q	q	T (2)	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

1. Terminal dimensions within this zone are uncontrolled.
2. Both recesses are ∅ 2.5 × 0.8 max. depth

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3-lead TO-220F				~~02-04-09~~ 06-02-14

Fig 8. Package outline SOT186A (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYQ28X-200_2	20090205	Product data sheet	-	BYQ28X_SERIES_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number BYQ28X-200 separated from data sheet BYQ28X_SERIES_1.			
BYQ28X_SERIES_1	19960801	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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12. Contents

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